

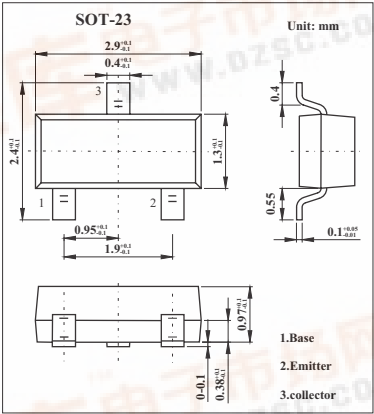
SMD Type

Transistors

NPN General Purpose Transistors
BCF81

■ Features

- Low current (max. 100 mA).
- Low voltage (max. 45 V).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	50	V
Collector-emitter voltage	V _{CE0}	45	V
Emitter-base voltage	V _{EB0}	5	V
Collector current	I _C	100	mA
Peak collector current	I _{CM}	200	mA
Peak base current	I _{BM}	100	mA
Total power dissipation *	P _{tot}	250	mW
Storage temperature	T _{stg}	-65 to +150	°C
Junction temperature	T _j	150	°C
Operating ambient temperature	R _{amb}	-65 to +150	°C
Thermal resistance from junction to ambient *	R _{th j-a}	500	K/W

* Transistor mounted on an FR4 printed-circuit board.

BCF81■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$I_E = 0; V_{CB} = 20\text{ V}$			100	nA
	I_{CBO}	$I_E = 0; V_{CB} = 20\text{ V}; T_j = 100^\circ\text{C}$			10	μA
Emitter cutoff current	I_{EBO}	$I_C = 0; V_{EB} = 5\text{ V}$			100	nA
DC current gain	h_{FE}	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	420		800	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$		120	250	mV
		$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$		210		mV
Base to emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$		750		mV
		$I_C = 50\text{ mA}; I_B = 2.5\text{ mA}$		850		mV
Base to emitter voltage	V_{BE}	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}$	550		700	mV
Collector capacitance	C_C	$I_E = I_C = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$		2.5		pF
Transition frequency	f_T	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100			MHz
Noise figure	NF	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$		1.2	4	dB

■ Marking

Marking	K9p
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